

BF256C N-Channel RF Amplifier Transistor



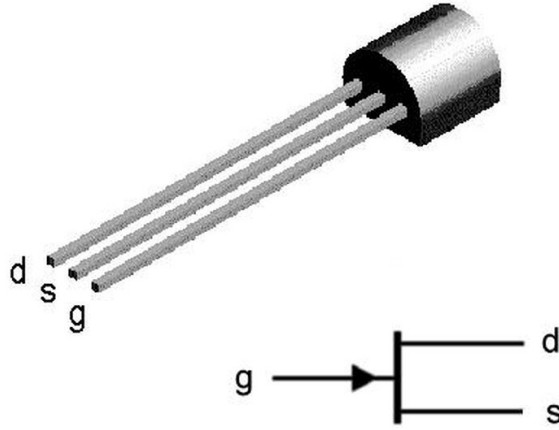
Features:

The BF256C N-Channel RF Amplifier Transistor is designed for VHF and UHF amplifier circuits. It is supplied in a TO-92 case and supports 30V drain-gate voltage, -30V gate-source voltage, 350 mW power dissipation, and operation across a -55°C to 150°C temperature range.

Specifications	
Part Number	BF256C
Device Type	N-channel RF amplifier transistor
Case	TO-92
Drain-Gate Voltage	30V
Gate-Source Voltage	-30V
Gate-Source Breakdown Voltage	-30V
Forward Gate Current	10 mA
Power Dissipation	350 mW
Derating Above 25°C	2.8 mW/°C
Input Capacitance Max	4.5 pF
Gate Reverse Current Max	-5 nA
Zero-Gate Voltage Drain Current	11 mA min, 18 mA max
Common Source Forward Transconductance	4.5 mmhos min
Vp Max	7.5V
Operating and Storage Temperature Range	-55°C to 150°C
Mounting Type	Through hole
Surface Mounted	No
Dimensions	1.9x0.4x0.3xm
Application	VHF and UHF amplifier circuits
Usage	RF signal amplification in VHF/UHF and electronic amplifier applications

Pinouts:

Pin Name	Description
G	Gate controls the transistor channel and switches or adjusts current flow between drain and source
S	Source reference terminal where current exits the channel
D	Drain terminal where current enters the channel



Product Pictures:

